BCR8CS-12LA

Triac

Medium Power Use

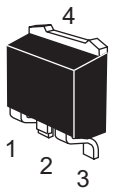
REJ03G0338-0300
Rev.3.00
Nov 30, 2007

Features

- $I_{T\,(RMS)}$: 8 A
- V_{DRM} : 600 V
- I_{FGTI}, I_{RGTI}, $I_{RGT\,III}$: 30 mA (20 mA)[Note6]
- Non-Insulated Type
- Planar Passivation Type

Outline

RENESAS Package code: PRSS0004AB-A
(Package name: TO-220S)



1. T_1 Terminal
2. T_2 Terminal
3. Gate Terminal
4. T_2 Terminal

Applications

Solid state relay, hybrid IC

Maximum Ratings

Parameter	Symbol	Voltage class	Unit
		12	
Repetitive peak off-state voltage[Note1]	V_{DRM}	600	V
Non-repetitive peak off-state voltage[Note1]	V_{DSM}	720	V

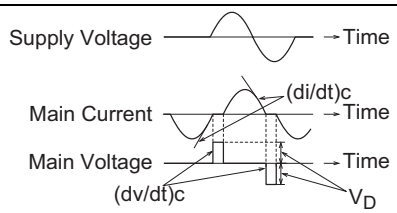
Parameter	Symbol	Ratings	Unit	Conditions
RMS on-state current	$I_{T\ (RMS)}$	8	A	Commercial frequency, sine full wave 360° conduction, Tc = 105°C[Note3]
Surge on-state current	I_{TSM}	80	A	60Hz sinewave 1 full cycle, peak value, non-repetitive
I^2t for fusing	I^2t	26	A^2s	Value corresponding to 1 cycle of half wave 60Hz, surge on-state current
Peak gate power dissipation	P_{GM}	5	W	
Average gate power dissipation	$P_{G\ (AV)}$	0.5	W	
Peak gate voltage	V_{GM}	10	V	
Peak gate current	I_{GM}	2	A	
Junction temperature	Tj	– 40 to +125	°C	
Storage temperature	Tstg	– 40 to +125	°C	
Mass	—	1.2	g	Typical value

Notes: 1. Gate open.

Electrical Characteristics

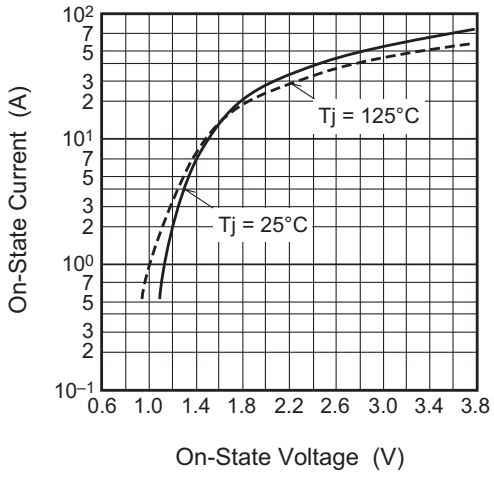
Parameter		Symbol	Min.	Typ.	Max.	Unit	Test conditions
Repetitive peak off-state current		I_{DRM}	—	—	2.0	mA	Tj = 125°C, V_{DRM} applied
On-state voltage		V_{TM}	—	—	1.5	V	Tc = 25°C, I_{TM} = 12 A, Instantaneous measurement
Gate trigger voltage[Note2]	I	V_{FGTI}	—	—	1.5	V	Tj = 25°C, V_D = 6 V, R_L = 6 Ω, R_G = 330 Ω
	II	V_{RGTI}	—	—	1.5	V	
	III	V_{RGTIII}	—	—	1.5	V	
Gate trigger current[Note2]	I	I_{FGTI}	—	—	30[Note6]	mA	Tj = 25°C, V_D = 6 V, R_L = 6 Ω, R_G = 330 Ω
	II	I_{RGTI}	—	—	30[Note6]	mA	
	III	I_{RGTIII}	—	—	30[Note6]	mA	
Gate non-trigger voltage		V_{GD}	0.2	—	—	V	Tj = 125°C, V_D = 1/2 V_{DRM}
Thermal resistance		$R_{th\ (j-c)}$	—	—	2.0	°C/W	Junction to case[Note3 Note4]
Critical-rate of rise of off-state commutating voltage[Note5]		(dv/dt)c	10	—	—	V/µs	Tj = 125°C

Notes: 2. Measurement using the gate trigger characteristics measurement circuit.
3. Case temperature is measured on the T_2 tab.
4. The contact thermal resistance $R_{th\ (c-f)}$ in case of greasing is 1.0°C/W.
5. Test conditions of the critical-rate of rise of off-state commutating voltage is shown in the table below.
6. High sensitivity ($I_{GT} \leq 20$ mA) is also available. (I_{GT} item: 1)

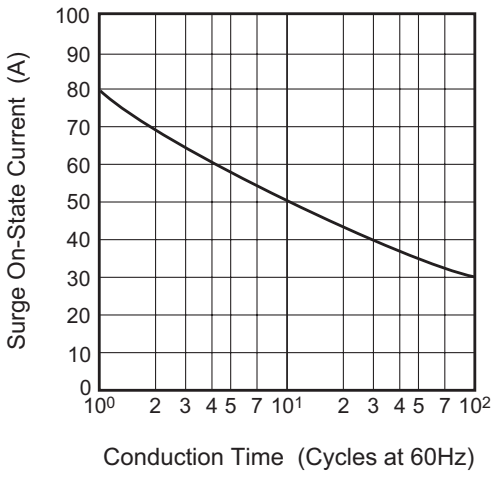
Test conditions	Commutating voltage and current waveforms (inductive load)
1. Junction temperature Tj = 125°C 2. Rate of decay of on-state commutating current (di/dt)c = – 4.0 A/ms 3. Peak off-state voltage V_D = 400 V	

Performance Curves

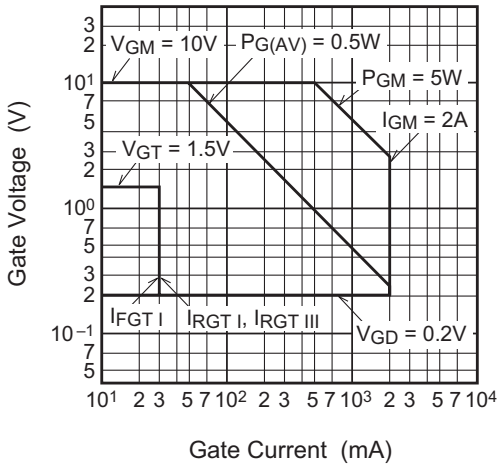
Maximum On-State Characteristics



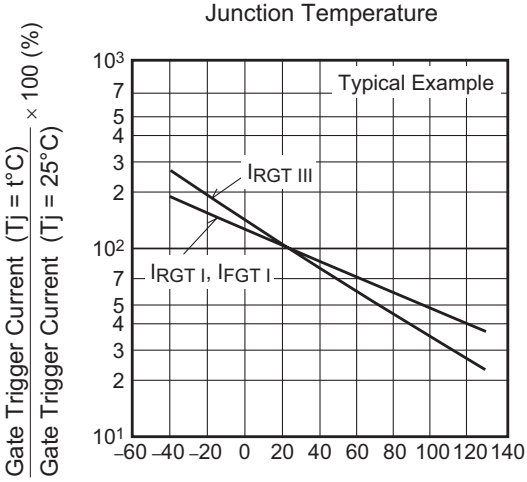
Rated Surge On-State Current



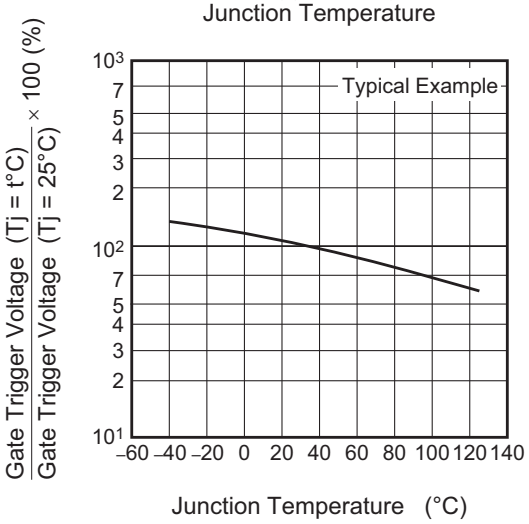
Gate Characteristics (I, II and III)



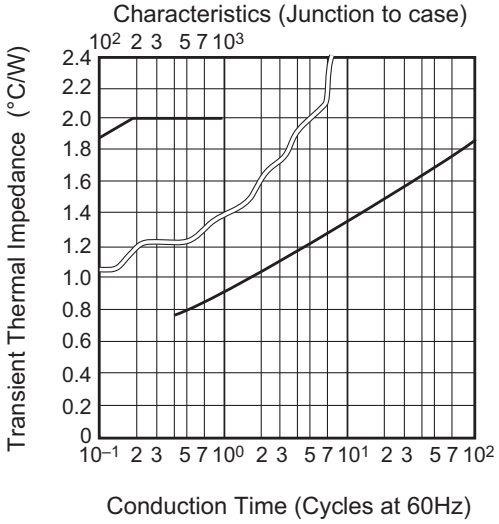
Gate Trigger Current vs. Junction Temperature



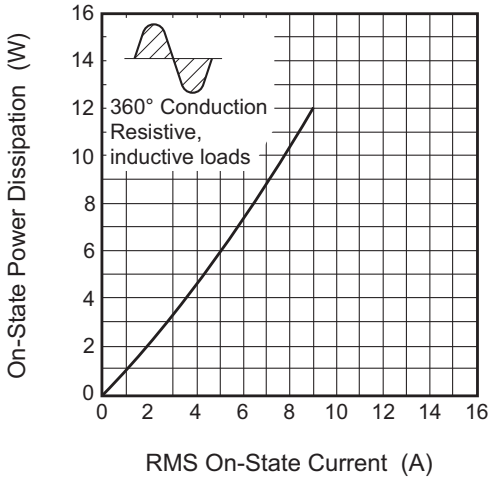
Gate Trigger Voltage vs. Junction Temperature



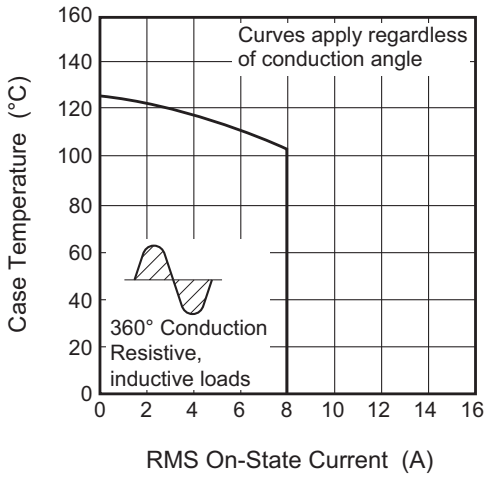
Maximum Transient Thermal Impedance Characteristics (Junction to case)



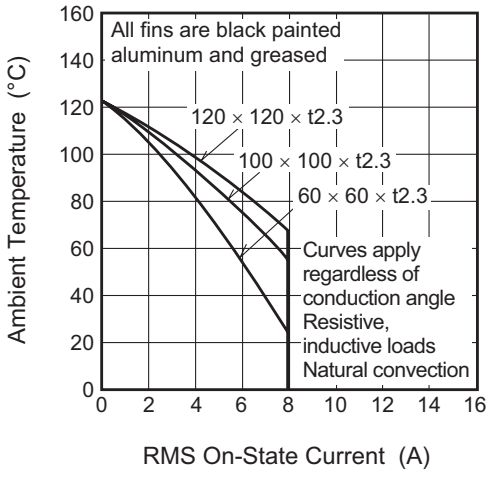
Maximum On-State Power Dissipation



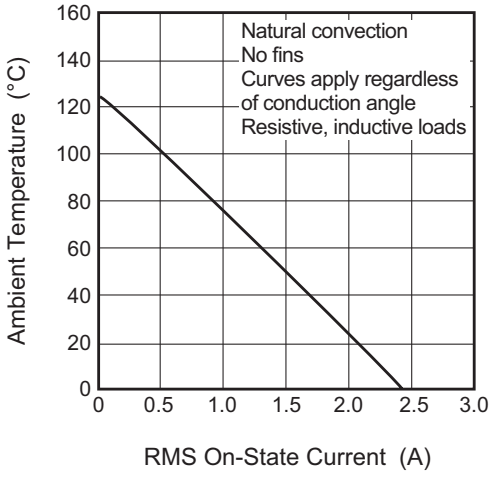
Allowable Case Temperature vs.
RMS On-State Current



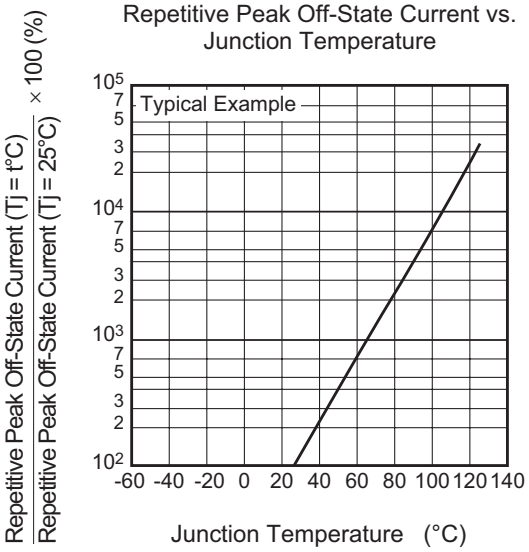
Allowable Ambient Temperature vs.
RMS On-State Current



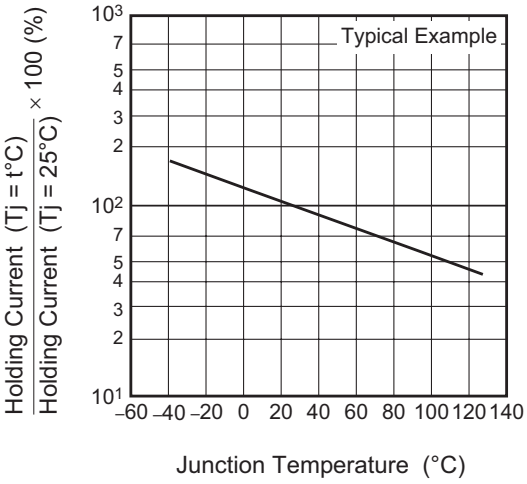
Allowable Ambient Temperature vs.
RMS On-State Current



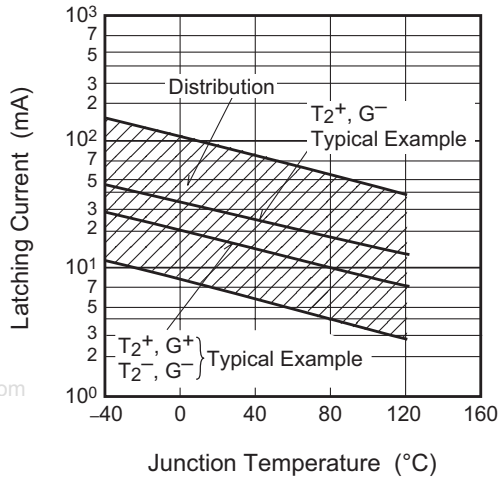
Repetitive Peak Off-State Current vs.
Junction Temperature



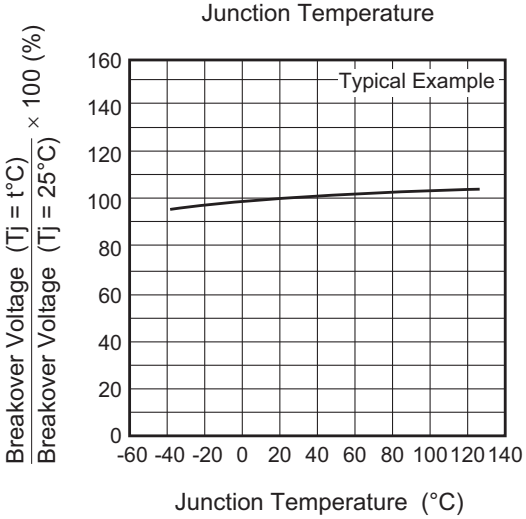
Holding Current vs.
Junction Temperature



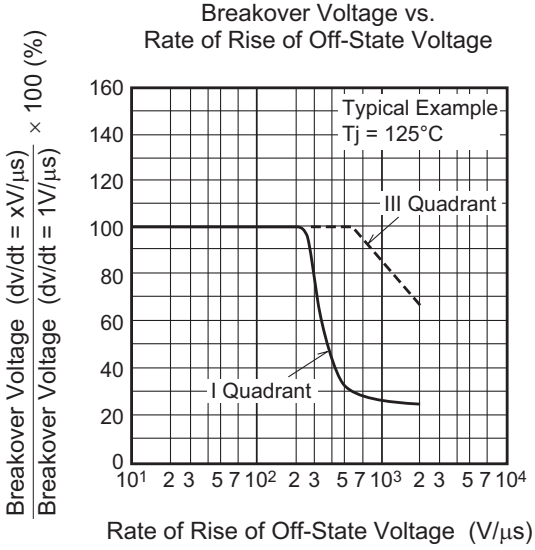
Latching Current vs.
Junction Temperature



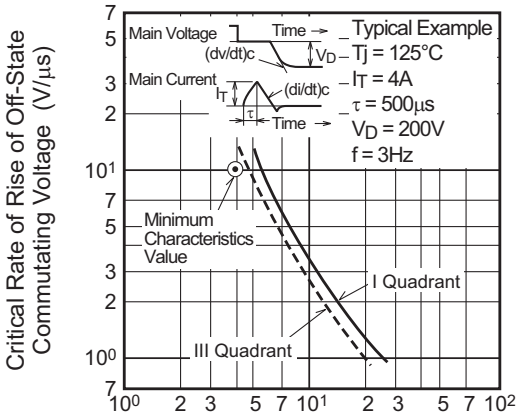
Breakover Voltage vs.
Junction Temperature



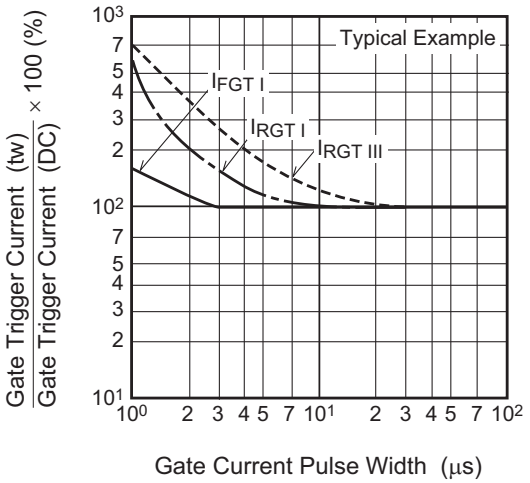
Breakover Voltage vs.
Rate of Rise of Off-State Voltage



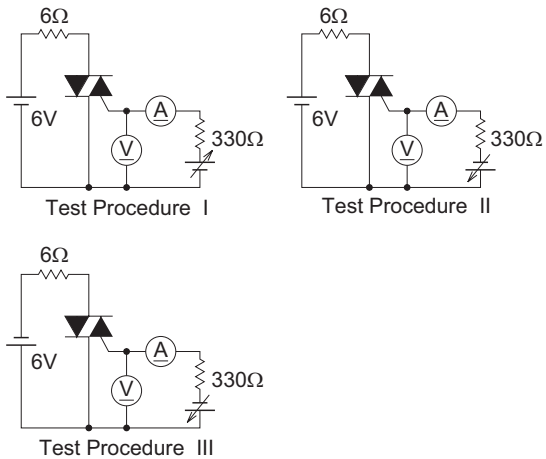
Commutation Characteristics



Gate Trigger Current vs.
Gate Current Pulse Width



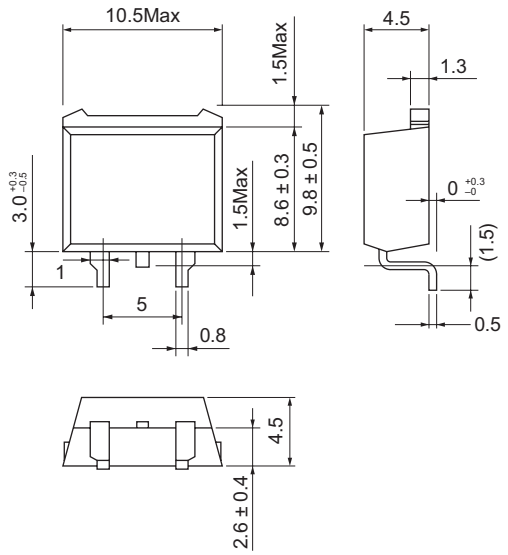
Gate Trigger Characteristics Test Circuits



Package Dimensions

Package Name	JEITA Package Code	RENESAS Code	Previous Code	MASS[Typ.]
TO-220S	SC-83	PRSS0004AB-A	TO-220S	1.2g

Unit: mm



Order Code

Lead form	Standard packing	Quantity	Standard order code	Standard order code example
Surface-mounted type	Taping	1000	Type name – T +Direction (1 or 2) +1	BCR8CS-12LA-T11
Surface-mounted type	Plastic Magazine (Tube)	50	Type name	BCR8CS-12LA

Note : Please confirm the specification about the shipping in detail.

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